

Silicon NPN Power Transistors

2SD2060

DESCRIPTION

www.datasheet4u.com

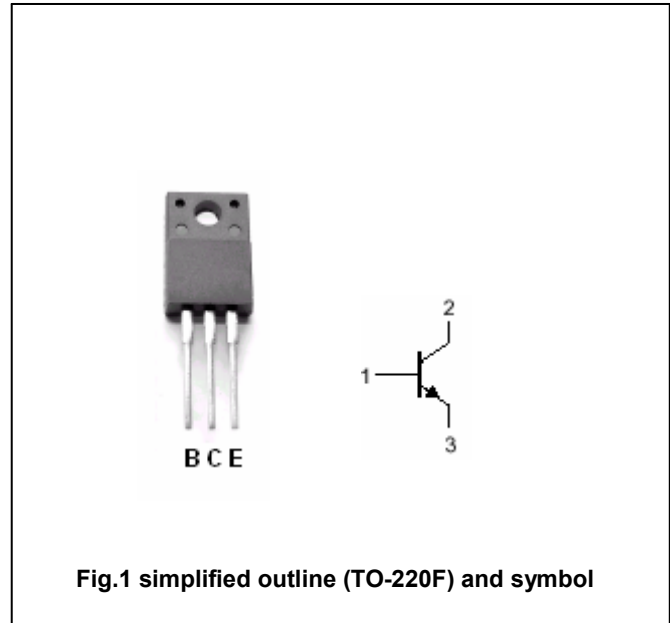
- With TO-220F package
- Complement to type 2SB1368
- Low collector saturation voltage:
 $V_{CE(SAT)}=1.7V(\text{Max})$ at $I_C=3A, I_B=0.3A$
- Collector power dissipation:
 $P_C=25W(T_C=25^\circ\text{C})$

APPLICATIONS

- With general purpose applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|---------------------------|------------------------|---------|------------------|
| V_{CBO} | Collector-base voltage | Open emitter | 80 | V |
| V_{CEO} | Collector-emitter voltage | Open base | 80 | V |
| V_{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I_C | Collector current | | 4 | A |
| I_B | Base current | | 0.4 | A |
| P_C | Collector dissipation | $T_a=25^\circ\text{C}$ | 2.0 | W |
| | | $T_C=25^\circ\text{C}$ | 25 | |
| T_j | Junction temperature | | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | | -55~150 | $^\circ\text{C}$ |

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =50mA ; I _B =0 | 80 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =10mA ; I _C =0 | 5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =3A ; I _B =0.3A | | 0.45 | 1.5 | V |
| V _{BE} | Base-emitter on voltage | I _C =3A ; V _{CE} =5V | | 1.0 | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =80V ; I _E =0 | | | 30 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =5V ; I _C =0 | | | 100 | μA |
| h _{FE-1} | DC current gain | I _C =0.5A ; V _{CE} =5V | 40 | | 240 | |
| h _{FE-2} | DC current gain | I _C =3A ; V _{CE} =5V | 15 | 50 | | |
| f _T | Transition frequency | I _C =0.5A ; V _{CE} =5V | | 8.0 | | MHz |
| C _{OB} | Collector output capacitance | f=1MHz ; V _{CB} =10V | | 90 | | pF |

◆ h_{FE-1} Classifications

| R | O | Y |
|-------|--------|---------|
| 40-80 | 70-140 | 120-240 |

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PACKAGE OUTLINE

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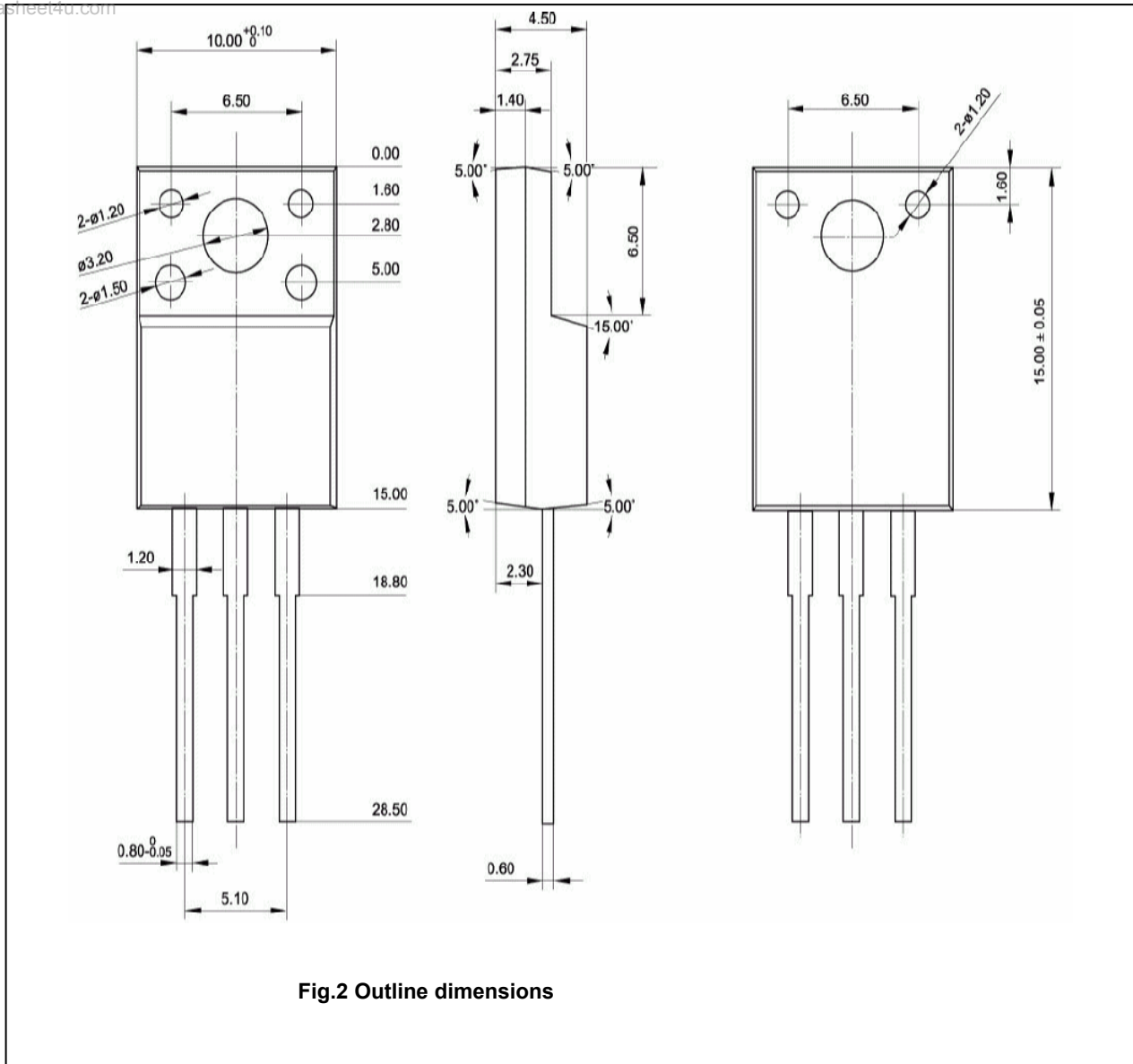


Fig.2 Outline dimensions

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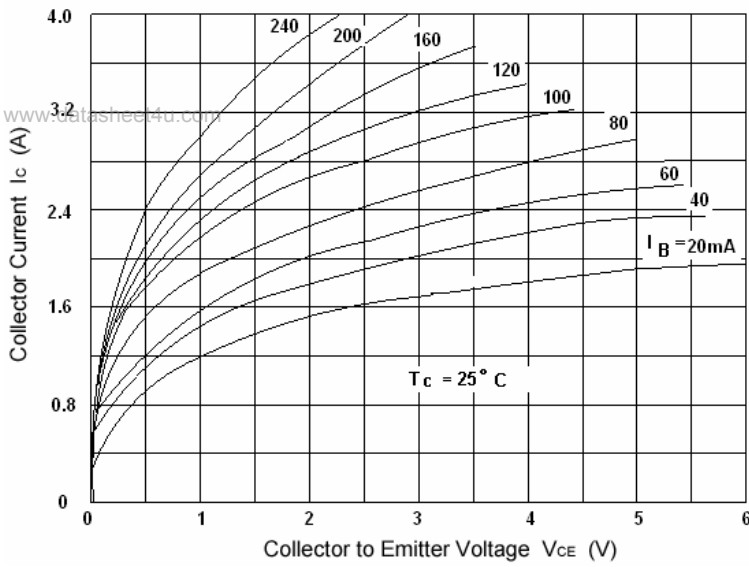


Fig.3 Static Characteristic

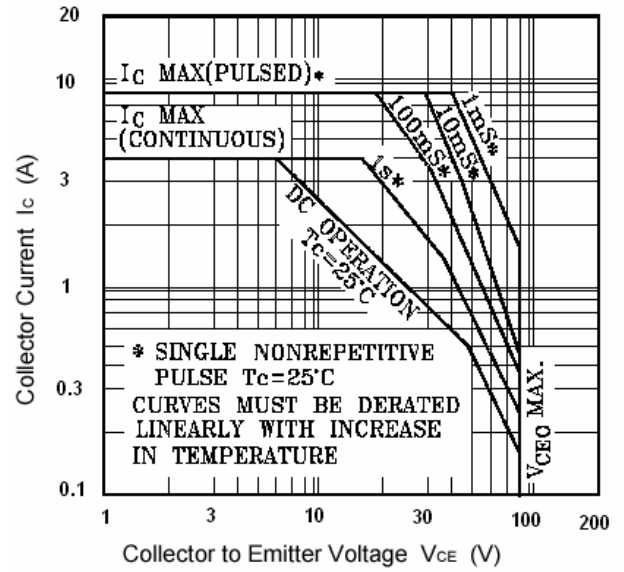


Fig.4 Safe Operating Area

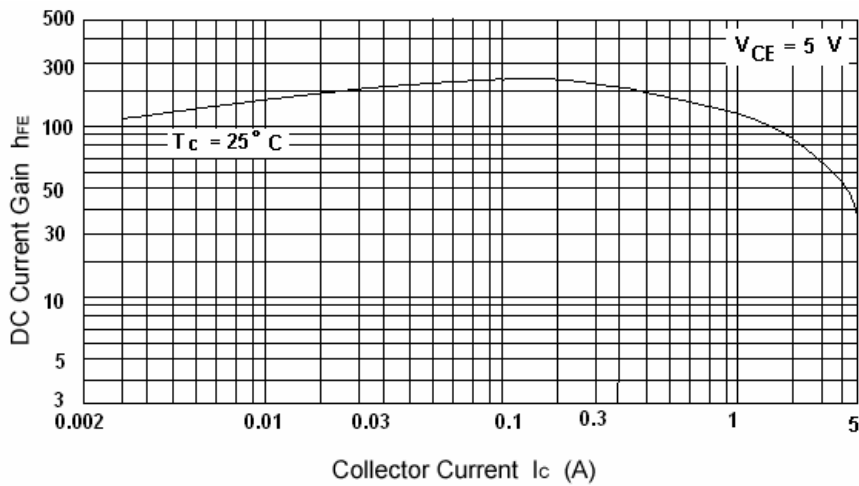


Fig.5 DC current Gain

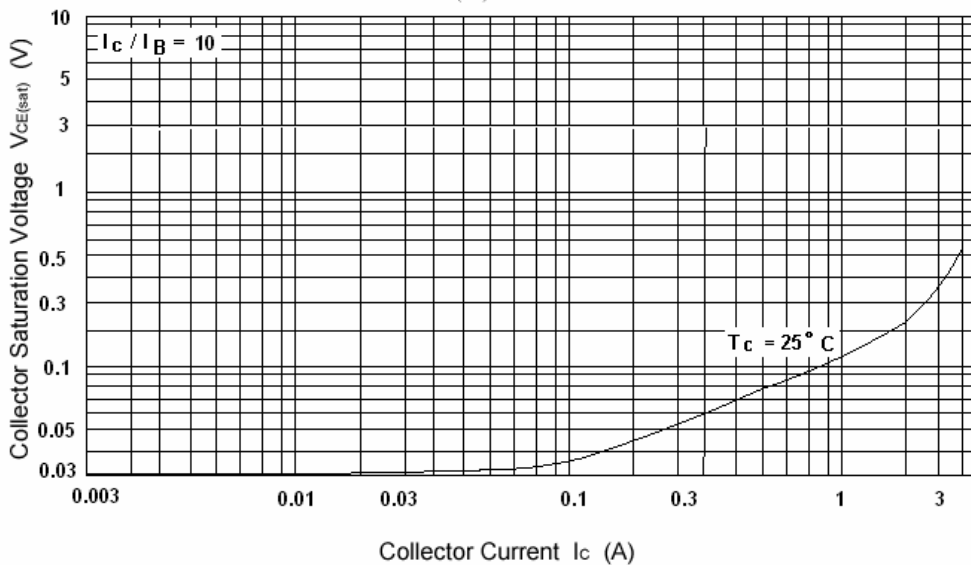


Fig.6 Base-Emitter Saturation Voltage